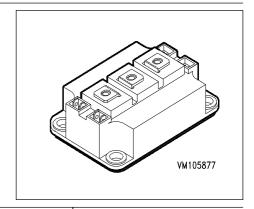


IGBT Power Module

- Half-bridge
- Including fast free-wheeling diodes
- Package with insulated metal base plate

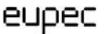


Туре	V _{CE}	I _C	Package	Ordering Code
BSM 200 GB 120 DN2	1200V	290A	HALF-BRIDGE 2	C67070-A2300-A70

Maximum Ratings

Parameter	Symbol	Values	Unit
Collector-emitter voltage	V _{CE}	1200	V
Collector-gate voltage	$V_{\rm CGR}$		
$R_{\rm GE}$ = 20 k Ω		1200	
Gate-emitter voltage	V_{GE}	± 20	
DC collector current	I _C		А
$T_{\rm C}$ = 25 °C		290	
<i>T</i> _C = 80 °C		200	
Pulsed collector current, $t_p = 1 \text{ ms}$	I _{Cpuls}		
$T_{\rm C}$ = 25 °C		580	
<i>T</i> _C = 80 °C		400	
Power dissipation per IGBT	P _{tot}		W
<i>T</i> _C = 25 °C		1400	
Chip temperature	$T_{\rm j}$	+ 150	∫°C
Storage temperature	$T_{ m stg}$	-40 + 125	
Thermal resistance, chip case	R_{thJC}	≤ 0.09	K/W
Diode thermal resistance, chip case	$R_{thJC\mathbf{D}}$	≤ 0.18	
Insulation test voltage, $t = 1$ min.	V _{is}	2500	Vac
Creepage distance	-	20	mm
Clearance	-	11	
DIN humidity category, DIN 40 040	-	F	sec
IEC climatic category, DIN IEC 68-1	-	40 / 125 / 56	

1



Electrical Characteristics, at $T_j = 25$ °C, unless otherwise specified

Parameter	Symbol		Values	;	Unit	
		min.	typ.	max.		
Static Characteristics						
Gate threshold voltage	V _{GE(th)}				V	
$V_{\text{GE}} = V_{\text{CE}}$, $I_{\text{C}} = 8 \text{ mA}$		4.5	5.5	6.5		
Collector-emitter saturation voltage	V _{CE(sat)}					
$V_{\rm GE}$ = 15 V, $I_{\rm C}$ = 200 A, $T_{\rm j}$ = 25 °C		-	2.5	3		
$V_{\rm GE}$ = 15 V, $I_{\rm C}$ = 200 A, $T_{\rm j}$ = 125 °C		-	3.1	3.7		
Zero gate voltage collector current	I _{CES}				mA	
$V_{CE} = 1200 \text{ V}, V_{GE} = 0 \text{ V}, T_j = 25 \text{ °C}$		-	3	4		
$V_{CE} = 1200 \text{ V}, V_{GE} = 0 \text{ V}, T_j = 125 \text{ °C}$		-	12	-		
Gate-emitter leakage current	I _{GES}				nA	
$V_{GE} = 20 \text{ V}, \ V_{CE} = 0 \text{ V}$		-	-	400		
AC Characteristics						
Transconductance	g_{fs}				S	
$V_{CE} = 20 \text{ V}, I_{C} = 200 \text{ A}$		108	-	-		
Input capacitance	C _{iss}				nF	
$V_{CE} = 25 \text{ V}, \ V_{GE} = 0 \text{ V}, \ f = 1 \text{ MHz}$		-	13	-		
Output capacitance	Coss					
$V_{CE} = 25 \text{ V}, \ V_{GE} = 0 \text{ V}, \ f = 1 \text{ MHz}$		-	2			
Reverse transfer capacitance	C _{rss}					
$V_{CE} = 25 \text{ V}, V_{GE} = 0 \text{ V}, f = 1 \text{ MHz}$		-	1	-		

 $T_{\rm j}$ = 125 °C



Electrical Characteristics, at T_j = 25 °C, unless otherwise specified Symbol Values

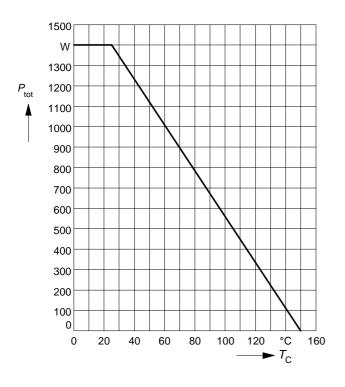
Parameter	Symbol	Values			Unit
		min.	typ.	max.	
Switching Characteristics, Inductive	Load at <i>T</i> _j =	: 125 °C			
Turn-on delay time	$t_{d(on)}$				ns
$V_{\rm CC}$ = 600 V, $V_{\rm GE}$ = 15 V, $I_{\rm C}$ = 200 A					
$R_{Gon} = 4.7 \Omega$		-	110	220	
Rise time	t_{r}				
$V_{\rm CC}$ = 600 V, $V_{\rm GE}$ = 15 V, $I_{\rm C}$ = 200 A					
$R_{Gon} = 4.7 \ \Omega$		-	80	160	
Turn-off delay time	$t_{d(off)}$				
$V_{\rm CC}$ = 600 V, $V_{\rm GE}$ = -15 V, $I_{\rm C}$ = 200 A					
$R_{\text{Goff}} = 4.7 \Omega$		-	550	800	
Fall time	t_{f}				
$V_{\rm CC}$ = 600 V, $V_{\rm GE}$ = -15 V, $I_{\rm C}$ = 200 A					
$R_{\text{Goff}} = 4.7 \Omega$		-	80	120	
Free-Wheel Diode					
Diode forward voltage	V _F				V
$I_{\rm F}$ = 200 A, $V_{\rm GE}$ = 0 V, $T_{\rm j}$ = 25 °C		-	2	2.5	
$I_{\rm F} = 200 \text{ A}, \ V_{\rm GE} = 0 \text{ V}, \ T_{\rm j} = 125 \text{ °C}$		-	1.8	-	
Reverse recovery time	<i>t</i> _{rr}				μs
$I_{\rm F}$ = 200 A, $V_{\rm R}$ = -600 V, $V_{\rm GE}$ = 0 V					
$d_{\rm F}/dt = -2000 \text{ A/\mus}, T_{\rm j} = 125 ^{\circ}\text{C}$		-	0.5	-	
Reverse recovery charge	Q _{rr}				μC
$I_{F} = 200 \text{ A}, \ V_{R} = -600 \text{ V}, \ V_{GE} = 0 \text{ V}$					
$d_{iF}/dt = -2000 \text{ A/}\mu\text{s}$					
<i>T</i> _j = 25 °C		-	12	-	
		1	1		



Power dissipation

 $P_{\mathsf{tot}} = f(T_{\mathsf{C}})$

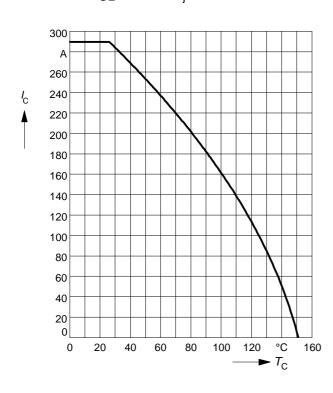
parameter: $T_j \le 150 \, ^{\circ}\text{C}$



Collector current

 $I_{\rm C}=f(T_{\rm C})$

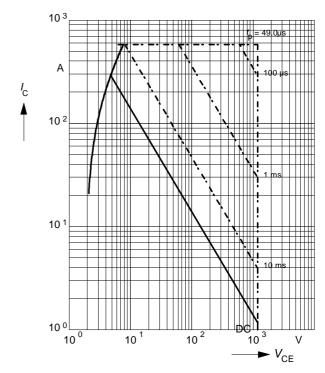
parameter: $V_{\text{GE}} \ge 15 \text{ V}$, $T_{\text{j}} \le 150 \text{ °C}$



Safe operating area

 $I_{\mathsf{C}} = f(V_{\mathsf{CE}})$

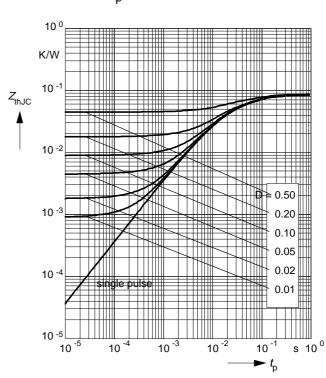
parameter: D = 0, $T_{C} = 25^{\circ}C$, $T_{i} \le 150 ^{\circ}C$



Transient thermal impedance IGBT

 $Z_{\text{th JC}} = f(t_{\text{p}})$

parameter: $D = t_p / T$

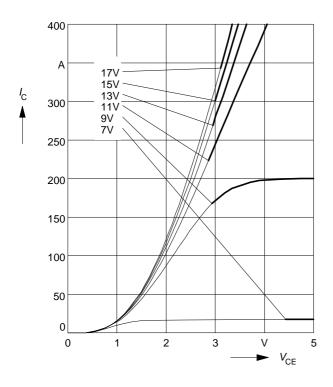




Typ. output characteristics

 $I_C = f(V_{CE})$

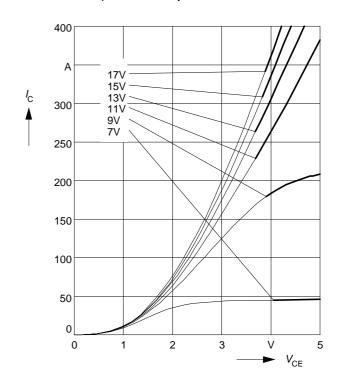
parameter: $t_p = 80 \mu s$, $T_j = 25 °C$



Typ. output characteristics

 $I_C = f(V_{CE})$

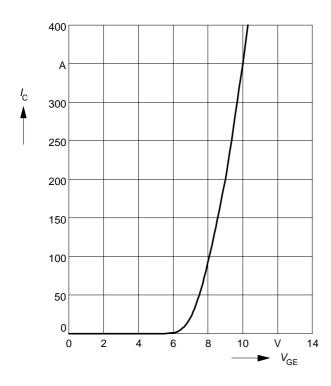
parameter: $t_p = 80 \mu s$, $T_j = 125 °C$



Typ. transfer characteristics

 $I_C = f(V_{GE})$

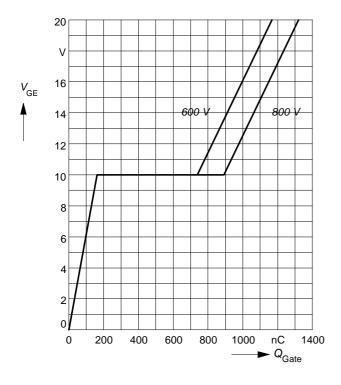
parameter: t_p = 80 μ s, V_{CE} = 20 V





Typ. gate charge

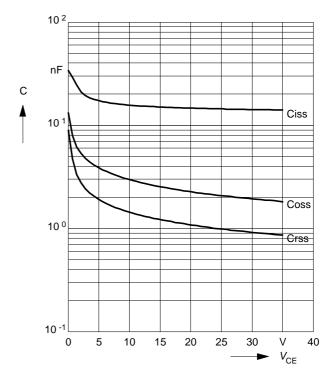
 $V_{\sf GE} = f(Q_{\sf Gate})$ parameter: $I_{\text{C puls}} = 200 \text{ A}$



Typ. capacitances

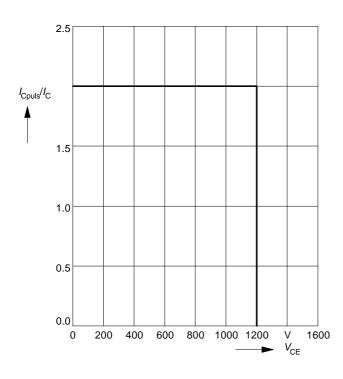
 $C = f(V_{CE})$

parameter: $V_{GE} = 0 \text{ V}, f = 1 \text{ MHz}$



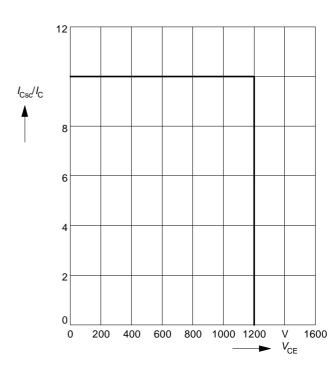
Reverse biased safe operating area

 $I_{Cpuls} = f(V_{CE})$, $T_j = 150$ °C parameter: $V_{GE} = 15$ V



Short circuit safe operating area

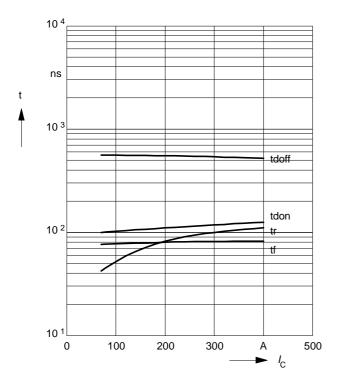
 I_{Csc} = $f(V_{CE})$, T_j = 150°C parameter: V_{GE} = ± 15 V, t_{SC} ≤ 10 μ s, L < 25 nH





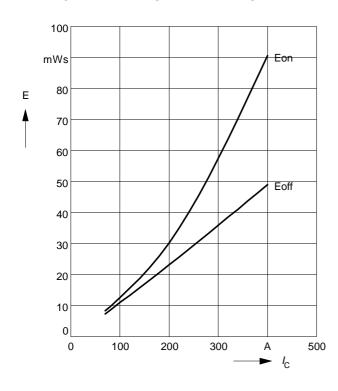
Typ. switching time

I=f (I_C) , inductive load , T_j = 125°C par.: V_{CE} = 600 V, V_{GE} = ± 15 V, R_G = 4.7 Ω



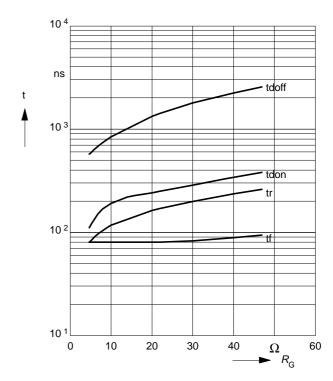
Typ. switching losses

E=f (I_C) , inductive load , $T_j=125^{\circ}C$ par.: $V_{CE}=600$ V, $V_{GE}=\pm15$ V, $R_G=4.7$ Ω



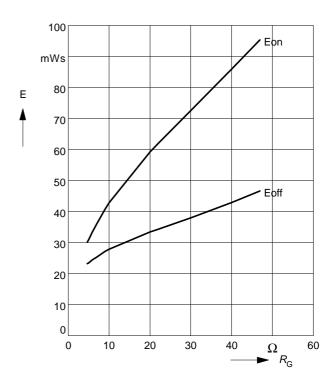
Typ. switching time

 $t = f(R_G)$, inductive load , $T_j = 125^{\circ}C$ par.: $V_{CE} = 600$ V, $V_{GE} = \pm 15$ V, $I_C = 200$ A



Typ. switching losses

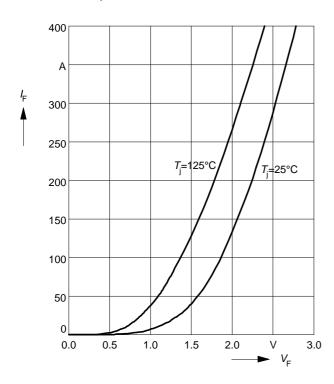
 $E = f(R_G)$, inductive load, $T_j = 125$ °C par.: $V_{CE} = 600$ V, $V_{GE} = \pm 15$ V, $I_C = 200$ A





Forward characteristics of fast recovery reverse diode $I_F = f(V_F)$

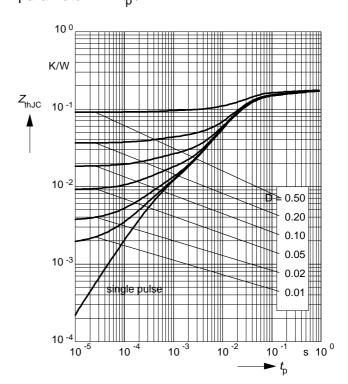
parameter: T_j



Transient thermal impedance Diode

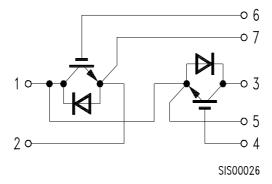
$$Z_{\text{th JC}} = f(t_{\text{p}})$$

parameter: $D = t_{\text{p}} / T$



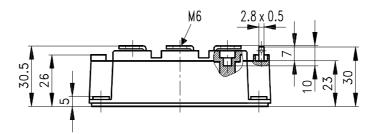


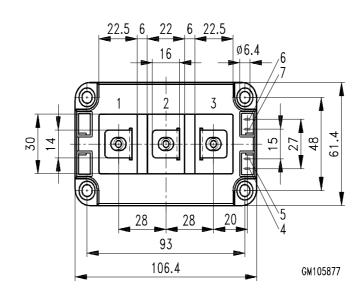
Circuit Diagram



Package Outlines

Dimensions in mm Weight: 420 g





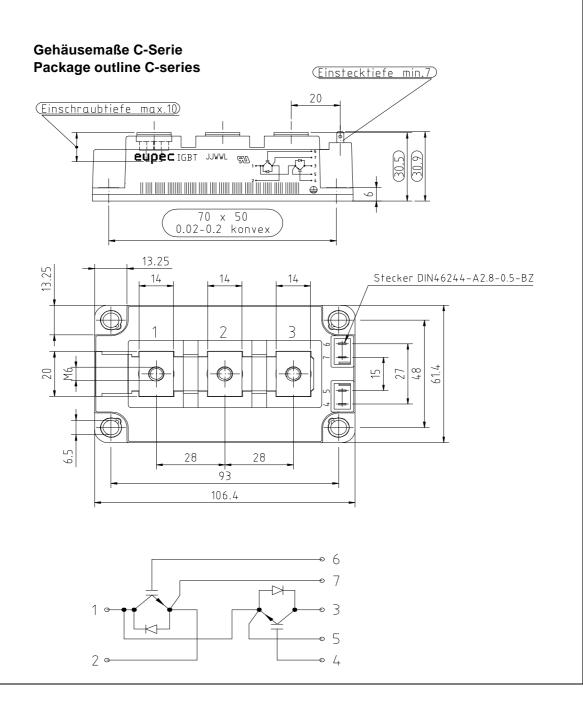
$\begin{tabular}{l} Technische Information / Technical Information \\ IGBT-Module \\ IGBT-Modules \\ \end{tabular} \begin{tabular}{l} BSM200GB120DN2 \\ \end{tabular}$



Anhang C-Serie Appendix C-series

Gehäuse spezifische Werte Housing specific values

	typ.			
Modulinduktivität stray inductance module		L _{sCE}	20	nH



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